

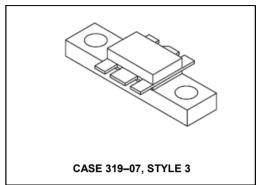
Rev. V1

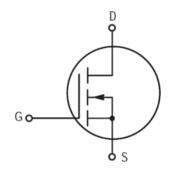
Designed primarily for wideband large–signal output and driver from 30–500MHz.

N-Channel enhancement mode MOSFET

- MRF166C Guaranteed performance at 500 MHz, 28 Vdc
 Output power = 20 W
 Gain = 13.5 dB
 Efficiency = 50%
- Replacement for industry standards such as MRF136, V2820, BLF244, SD1902, and ST1001
- 100% tested for load mismatch at all phase angles with 30:1 VSWR
- · Facilitates manual gain control, ALC and modulation techniques
- · Excellent thermal stability, ideally suited for Class A operation
- Low Crss 4.0 pF @ VDS = 28 V

Product Image





MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V _{DSS}	65	Vdc
Drain-Gate Voltage (RGS = 1.0 MΩ)	VDGR	65	Vdc
Gate-Source Voltage	V _{GS} ±20		Adc
Drain Current — Continuous	ΙD	4.0	Adc
Total Device Dissipation @ T _C = 25°C Derate Above 25°C	PD	70 0.4	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to 150	°C
Operating Junction Temperature	TJ	200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _θ JC	2.5	°C/W

 $\label{eq:NOTE-Delta-CAUTION} \textbf{MOS}\ devices\ are\ susceptible\ to\ damage\ from\ electrostatic\ charge.\ Reasonable\ precautions\ in\ handling\ and\ packaging\ MOS\ devices\ should\ be\ observed.$

MRF166C



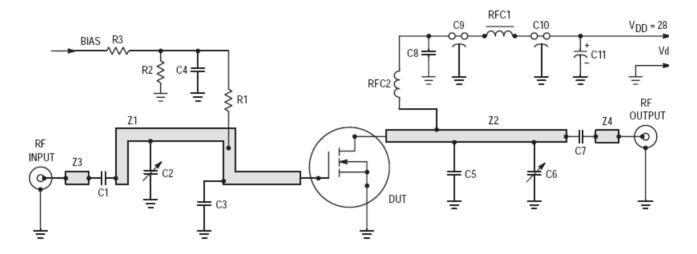
The RF MOSFET Line 20W, 500MHz, 28V

Rev. V1

ELECTRICAL CHARACTERISTICS (TC = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		•
Drain–Source Breakdown Voltage (V _{GS} = 0 V, I _D = 5.0 mA)	V _{(BR)DSS}	65	_	_	٧
Zero Gate Voltage Drain Current (VDS = 28 V, VGS = 0 V)	IDSS	_	_	0.5	mA
Gate-Source Leakage Current (VGS = 20 V, VDS = 0 V)	IGSS	_	_	1.0	μА
ON CHARACTERISTICS			•		•
Gate Threshold Voltage (V _{DS} = 10 V, I _D = 25 mA)	VGS(th)	1.5	3.0	4.5	٧
Forward Transconductance (V _{DS} = 10 V, I _D = 1.5 A)	9fs	0.8	1.1	_	mhos
DYNAMIC CHARACTERISTICS			•		•
Input Capacitance (VDS = 28 V, VGS = 0 V, f = 1.0 MHz)	C _{iss}	_	28	_	pF
Output Capacitance (V _{DS} = 28 V, V _{GS} = 0 V, f = 1.0 MHz)	C _{oss}	_	30	_	pF
Reverse Transfer Capacitance (VDS = 28 V, VGS = 0 V, f = 1.0 MHz)	C _{rss}	_	4.0	_	pF
FUNCTIONAL CHARACTERISTICS			•		•
Common Source Power Gain (V _{DD} = 28 V, P _{out} = 20 W, f = 500 MHz, I _{DQ} = 25 mA)	G _{ps}	13.5	16	_	dB
Drain Efficiency (V _{DD} = 28 V, P _{out} = 20 W, f = 500 MHz, I _{DQ} = 25 mA)	η	50	55	_	%
Electrical Ruggedness (VDD = 28 V, Pout = 20 W, f = 500 MHz, IDQ = 25 mA, Load VSWR 30:1 at All Phase Angles)	Ψ	No Degradation in Output Power			





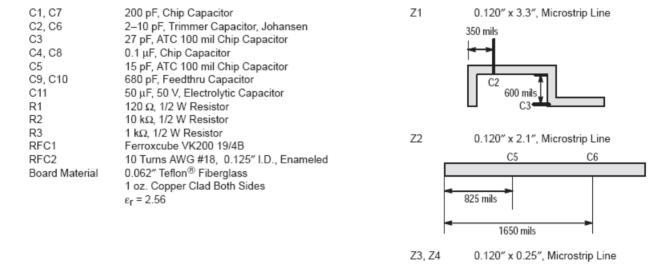


Figure 1. MRF166C 500 MHz Test Circuit



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TYPICAL CHARACTERISTICS

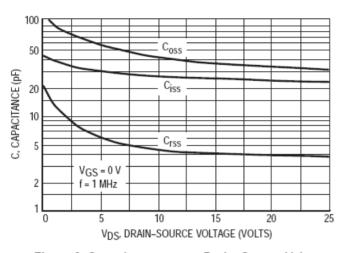


Figure 2. Capacitance versus Drain-Source Voltage

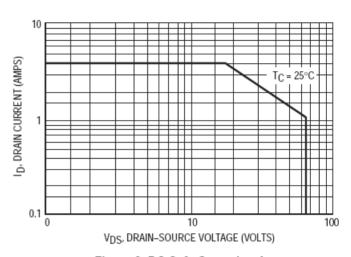


Figure 3. DC Safe Operating Area

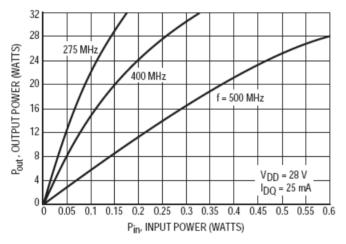


Figure 4. Output Power versus Input Power

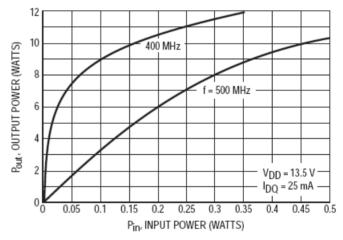
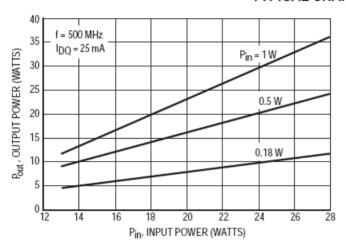


Figure 5. Output Power versus Input Power



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TYPICAL CHARACTERISTICS



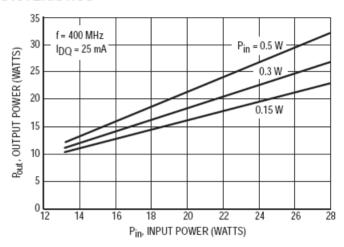
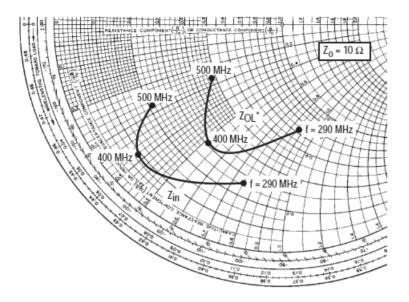


Figure 6. Output Power versus Supply Voltage

Figure 7. Output Power versus Supply Voltage





f MHz) = 28 V, I _{DQ} = 25 mA, P Z _{in} Ohms	Z _{OL} * Ohms
500	2.09 – j2.77	4.87 – j2.63
400	0.93 – j3.80	3.09 – j5.24
290	2.63 – j7.58	7.35 – j8.67

Z_{OL}* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 8. Series Equivalent Input and Output Impedance

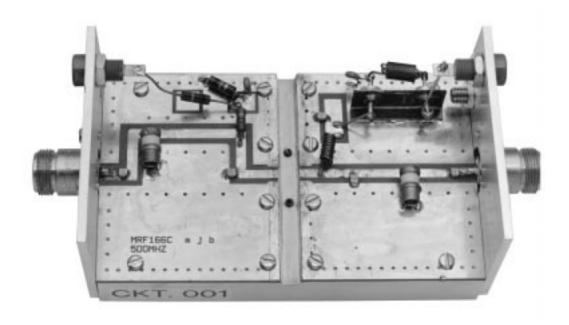


Figure 9. MRF166C Test Fixture



Table 1. Common Source S-Parameters (VDS = 12.5 V, ID = 1.25 A)

f	s	11	S	21	S ₁₂		\$22		
MHz	S ₁₁	ф	\$ ₂₁	ф	S ₁₂	ф	S ₂₂	ф	
30	0.840	-142	22.59	105	0.025	20	0.727	-155	
40	0.836	-151	17.4	100	0.025	17	0.743	-161	
50	0.832	-156	14.1	97	0.026	15	0.751	-164	
60	0.829	-159	12.0	94	0.026	14	0.764	-166	
70	0.826	-162	10.4	91	0.026	14	0.763	-168	
80	0.822	-164	9.09	90	0.026	14	0.763	-169	
90	0.818	-165	8.07	89	0.027	14	0.765	-170	
100	0.819	-167	7.28	87	0.027	14	0.774	-171	
110	0.821	-168	6.61	85	0.027	14	0.773	-172	
120	0.821	-169	6.00	83	0.026	15	0.771	-172	
130	0.820	-169	5.56	83	0.027	16	0.778	-172	
140	0.818	-170	5.22	82	0.027	17	0.785	-172	
150	0.820	-170	4.86	80	0.027	17	0.786	-173	
160	0.821	-171	4.52	79	0.027	17	0.781	-173	
170	0.820	-171	4.23	79	0.027	20	0.774	-172	
180	0.820	-171	4.03	78	0.027	20	0.799	-173	
190	0.820	-172	3.86	76	0.027	20	0.799	-174	
200	0.821	-172	3.62	75	0.027	20	0.784	-175	
210	0.822	-173	3.39	75	0.027	22	0.780	-174	
220	0.823	-173	3.25	74	0.027	24	0.795	-173	
230	0.825	-173	3.12	72	0.028	23	0.823	-175	
240	0.827	-173	2.96	71	0.026	24	0.791	-175	
250	0.827	-174	2.83	70	0.027	26	0.789	-174	
260	0.827	-174	2.71	70	0.026	27	0.791	-174	
270	0.829	-174	2.62	69	0.027	28	0.801	-174	
280	0.831	-174	2.52	68	0.027	29	0.807	-175	
290	0.832	-174	2.42	66	0.027	30	0.788	-175	
300	0.832	-174	2.32	66	0.027	32	0.792	-175	
310	0.831	-174	2.25	66	0.027	33	0.797	-174	
320	0.833	-175	2.18	65	0.027	34	0.810	-174	
330	0.836	-175	2.10	63	0.028	35	0.812	-175	
340	0.837	-175	2.00	62	0.027	35	0.789	-176	
350	0.838	-175	1.95	62	0.028	39	0.806	-173	
360	0.839	-175	1.90	61	0.028	39	0.817	-174	
370	0.840	-176	1.84	60	0.028	40	0.817	-175	
380	0.843	-176	1.77	59	0.028	41	0.811	-175	
390	0.845	-176	1.71	59	0.028	42	0.805	-175	
400	0.846	-176	1.66	58	0.029	46	0.801	-172	
410	0.846	-176	1.64	57	0.030	46	0.845	-174	
420	0.847	-176	1.59	56	0.030	46	0.836	-176	
430	0.848	-176	1.52	56	0.030	47	0.823	-176	
440	0.850	-176	1.48	56	0.030	49	0.816	-174	



Table 1. Common Source S-Parameters (VDS = 12.5 V, ID = 1.25 A) (continued)

f S		11	S	21	S.	12	s ₂₂	
MHz	S ₁₁	ф	\$ ₂₁	ф	\$ ₁₂	ф	\$ ₂₂	ф
450	0.851	-176	1.47	54	0.032	51	0.851	-174
460	0.853	-177	1.42	53	0.032	48	0.849	-178
470	0.853	-177	1.37	53	0.031	51	0.830	-176
480	0.856	-177	1.34	53	0.032	53	0.834	-176
490	0.857	-177	1.32	52	0.033	54	0.841	-175
500	0.859	-177	1.28	51	0.034	54	0.847	-175
600	0.857	178	0.988	41	0.032	73	0.877	180
700	0.884	176	0.789	34	0.047	65	0.881	179
800	0.881	173	0.684	30	0.031	83	0.890	174
900	0.890	172	0.580	26	0.069	71	0.885	176
1000	0.897	170	0.503	24	0.090	60	0.931	173



Table 2. Common Source S-Parameters (VDS = 28 V, ID = 1.25 A)

f	f S ₁₁		s ₂₁		s	S ₁₂		s ₂₂	
MHz	S ₁₁	ф	S ₂₁	ф	S ₁₂	ф	\$ ₂₂	ф	
30	0.842	-125	29.6	113	0.024	28	0.586	-136	
40	0.831	-136	23.2	106	0.025	22	0.607	-145	
50	0.822	-143	19.0	101	0.026	19	0.613	-151	
60	0.816	-148	16.2	98	0.026	17	0.626	-155	
70	0.812	-152	14.1	95	0.027	16	0.635	-157	
80	0.806	-155	12.4	92	0.026	15	0.643	-159	
90	0.801	-157	11.1	90	0.027	14	0.650	-160	
100	0.802	-159	9.97	88	0.027	13	0.656	-161	
110	0.805	-161	9.04	86	0.027	13	0.654	-163	
120	0.805	-162	8.22	84	0.026	13	0.654	-163	
130	0.803	-163	7.59	83	0.026	14	0.663	-163	
140	0.801	-164	7.09	82	0.026	14	0.673	-164	
150	0.803	-165	6.61	80	0.026	14	0.675	-164	
160	0.804	-165	6.16	79	0.026	14	0.674	-164	
170	0.803	-166	5.77	78	0.026	16	0.672	-164	
180	0.804	-166	5.49	77	0.026	17	0.697	-164	
190	0.806	-166	5.25	75	0.026	16	0.700	-165	
200	0.806	-167	4.92	73	0.025	16	0.688	-166	
210	0.807	-168	4.60	73	0.025	17	0.680	-165	
220	0.809	-168	4.40	72	0.025	19	0.689	-165	
230	0.812	-168	4.21	70	0.025	19	0.713	-167	
240	0.814	-169	3.99	69	0.024	20	0.701	-167	
250	0.815	-169	3.83	68	0.024	21	0.707	-166	
260	0.816	-169	3.66	67	0.024	22	0.711	-166	
270	0.818	-169	3.52	66	0.024	23	0.715	-166	
280	0.821	-169	3.39	65	0.025	24	0.718	-167	
290	0.822	-170	3.25	63	0.024	26	0.708	-168	
300	0.823	-170	3.11	62	0.023	28	0.715	-167	



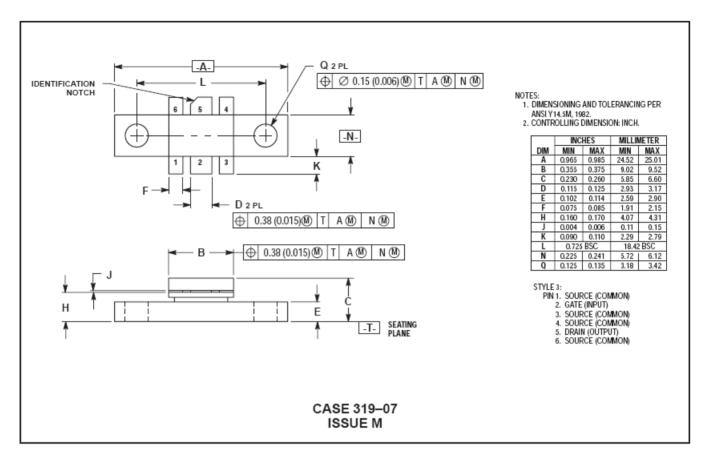
Table 2. Common Source S-Parameters (VDS = 28 V, ID = 1.25 A) (continued)

f	f S ₁₁		s ₂₁		S	12	s ₂₂	
MHz	S ₁₁	ф	\$ ₂₁	ф	S ₁₂	ф	\$ ₂₂	ф
310	0.822	-170	2.99	62	0.023	29	0.725	-166
320	0.825	-170	2.89	61	0.024	31	0.734	-166
330	0.828	-171	2.78	60	0.024	33	0.736	-167
340	0.830	-171	2.66	59	0.024	33	0.724	-168
350	0.832	-171	2.59	58	0.024	37	0.739	-166
360	0.834	-171	2.52	57	0.024	39	0.757	-166
370	0.836	-171	2.44	56	0.023	39	0.755	-167
380	0.839	-172	2.34	55	0.023	38	0.745	-167
390	0.840	-172	2.26	54	0.024	40	0.738	-168
400	0.841	-172	2.19	54	0.024	46	0.735	-166
410	0.842	-172	2.14	53	0.025	46	0.787	-167
420	0.844	-172	2.09	51	0.026	46	0.790	-168
430	0.845	-173	1.99	51	0.027	49	0.777	-168
440	0.846	-173	1.93	51	0.026	52	0.770	-167
450	0.849	-173	1.91	49	0.027	53	0.794	-167
460	0.853	-173	1.84	48	0.027	51	0.803	-171
470	0.855	-173	1.77	47	0.027	54	0.787	-170
480	0.857	-174	1.72	47	0.027	57	0.789	-169
490	0.857	-174	1.68	47	0.027	56	0.796	-168
500	0.859	-174	1.64	46	0.029	57	0.802	-169
600	0.862	-179	1.18	33	0.036	77	0.851	-173
700	0.893	178	0.921	26	0.043	75	0.856	-175
800	0.890	175	0.771	22	0.043	78	0.880	-178
900	0.895	173	0.635	17	0.065	74	0.882	-178
1000	0.905	171	0.544	14	0.086	69	0.931	178



Rev. V1

PACKAGE DIMENSIONS



MRF166C



The RF MOSFET Line 20W, 500MHz, 28V

Rev. V1

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